





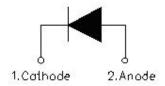
SDUR60V60W ULTRAFAST RECTIFIER



Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features:

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Plastic Material has UL Flammability Classification 94V-O
- Terminals finish: 100% Pure Tin
- This is a Pb free device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	600	V
Average Rectified Forward Current	I _{F (AV)}	Tc=140°C	60	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse, T _J =25°C	400	Α







Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 60A, Pulse, T _J = 25°C	1.18	1.70	V
	V_{F2}	@ 60A, Pulse, T _J = 150°C	1.08	1.60	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J =25°C	0.02	10	uA
	I _{R2}	@V _R = rated V _R , T _J =150°C	0.05	1	mA
Reverse Recovery Time	t _{rr1}	I _F =500mA,I _R =1A,and I _m =250mA, T _J =25°C	80	100	ns
Reverse Recovery Time	t _{rr}		49	-	ns
Reverse Recovery Charge	Q _{rr}	$I_F = 1A$, diF/dt = 100A/ μ s $V_R = 30V$, $T_J = 25$ °C	78	-	nC
Reverse Recovery Current	I _{RRM}	VR 56V, 1, 25 C	3	-	Α
Reverse Recovery Time	t _{rr}	I _F = 30A, diF/dt = 200A/μs	147	-	ns
Reverse Recovery Charge	Q _{rr}	V _R = 300V, T _J = 25°C	765	-	nC
Reverse Recovery Current	I _{RRM}		10.4	-	Α
Reverse Recovery Time	t _{rr}	I _F = 30A, diF/dt = 200A/µs	223	-	ns
Reverse Recovery Charge	Q _{rr}	$V_R = 300V, T_J = 125^{\circ}C$	1964	-	nC
Reverse Recovery Current	I _{RRM}		18	-	Α

 $^{^{\}star}$ Pulse width < 300 μ s, duty cycle < 2%



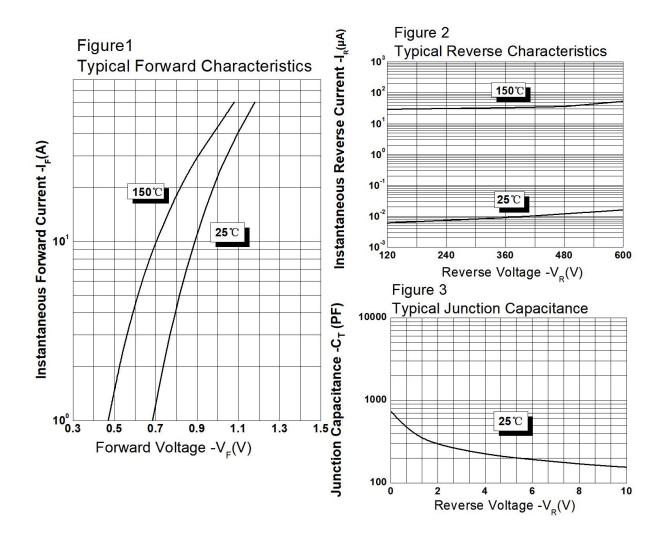




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units	
Junction Temperature	T_J	-	-55 to +175	°C	
Storage Temperature	T_{stg}	-	-55 to +175	°C	
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.34	°C/W	
Approximate Weight	wt	-	6.28	g	
Case Style	TO-247AC				

Ratings and Characteristics Curves



[•] China - Germany - Korea - Singapore - United States •

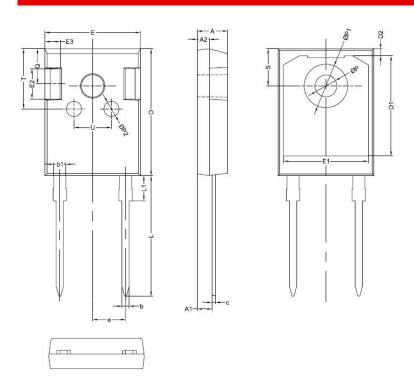
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Mechanical Dimensions TO-247AC

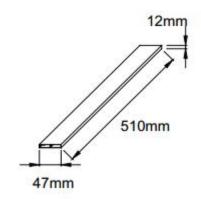


0/44501	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.35		
b1	1.80	2.00	2.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.58			
D2 E		1.17			
E	15.60	15.80	16.00		
E1		14.02			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.42		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1	7.19	7.40		
P2		2.50			
Q		5.80			
Q S	6.05	6.15	6.25		
Т		10.00			
U		6.20			

Ordering Information

Device	Package	Plating	Shipping	
SDUR60V60W	TO-247AC(Pb-Free)	Pure Sn	25pcs / tube	

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

= Device Type = Forward Current (60A) SDUR 60 60 = Reverse Voltage (600V)

= Configuration

W SSG YY = SSG = Year ww = Week = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •

SDUR60V60W



Technical Data Data Sheet N2449, Rev.B





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